NSN 5961-01-065-8073

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-065-8073
Inclosure Material:
Metal
Overall Length:
Between 0.250 inches and 0.450 inches
Overall Diameter:
0.875 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
То-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
160.0 breakdown voltage, collector-to-base, emitter open and 7.0 breakdown voltage, emitter-to-base, collector open and 140.0
breakdown voltage, collector-to-emitter, base open
Current Rating Per Characteristic:
10.00 amperes source cutoff current and 7.00 amperes source cutoff current
Power Rating Per Characteristic:
4.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 2 pin
Specification Data:
81349-mil-s-19500/370/navy/ government specification
Shelf Life:
N/a
Unit Of Measure:

N

Demilitarization:

NSN 5961-01-065-8073 Transistor - Page 2 of 2



Fiig:

A110a0